









LSF0101, LSF0102, LSF0108 SDLS966K - DECEMBER 2013 - REVISED MAY 2021

LSF010x 1/2/8 Channel Auto-Bidirectional Multi-Voltage Level Translator for Open-**Drain and Push-Pull Applications**

1 Features

- Provides bidirectional voltage translation with no direction pin
- Supports up to 100-MHz up translation and greater than 100-MHz down translation at ≤ 30pF cap load and up To 40-MHz up/down translation at 50pF cap load
- Allows bidirectional voltage-level translation between
 - 0.95 V \leftrightarrow 1.8/2.5/3.3/5 V
 - 1.2 V ↔ 1.8/2.5/3.3/5 V
 - $1.8 \text{ V} \leftrightarrow 2.5/3.3/5 \text{ V}$
 - 2.5 V ↔ 3.3/5 V
 - $3.3 \text{ V} \leftrightarrow 5 \text{ V}$
- Low standby current
- 5-V tolerance I/O port to support TTL
- Low R_{ON} provides less signal distortion
- High-impedance I/O pins for EN = Low
- Flow-through pinout for easy PCB trace routing
- Latch-up performance >100 mA per JESD 17
- -40°C to 125°C Operating temperature range

2 Applications

- GPIO, MDIO, PMBus, SMBus, SDIO, UART, I²C, and other interfaces in telecom infrastructure
- Enterprise systems
- Communications equipment
- Personal electronics
- Industrial applications

3 Description

The LSF family of devices supports bidirectional voltage translation without the need for DIR pin which minimizes system effort (for PMBus, I²C, SMBus, etc.). The LSF family of devices supports up to 100-MHz up translation and greater than 100-MHz down translation at ≤ 30pF cap load and up to 40-MHz up/down translation at 50pF cap load which allows the LSF family to support more consumer or telecom interfaces (MDIO or SDIO).

LSF family supports 5-V tolerance on I/O port which makes it compatible with TTL levels in industrial and telecom applications. The LSF family is able to set up different voltage translation levels on each channel which makes it very flexible.

Device Information

PART NUMBER	PACKAGE(PINS)(1)	BODY SIZE (NOM)		
LSF0101DRY	SON (6)	1.45 mm × 1.00 mm		
LSF0101DTQ	X2SON (6)	1.00 mm x 0.80 mm		
LSF0102DQE	X2SON (8)	1.40 mm × 1.00 mm		
LSF0102YZT	DSBGA (8)	1.90 mm × 1.00 mm		
LSF0102DCT	SM8 (8)	2.80 mm × 2.95 mm		
LSF0102DCU	VSSOP (8)	2.30 mm × 2.00 mm		
LSF0108RKS	VQFN (20)	4.50 mm × 2.50 mm		
LSF0108PW	TSSOP (20)	4.40 mm × 6.50 mm		

For all available packages, see the orderable addendum at the end of the data sheet.

LSF0101 LSF0102 LSF0108 DTQ Package DRY Package YZT Package DOF Package RKS Package 6-Pin SON 8-Pin DSBGA 8-Pin X2SON 20-Pin VQFN 6-Pin X2SON Transparent Top View Transparent Top View Transparent Top View Transparent Top View **Bottom View** GND EN GND EN A2 📵 @ B2 GND 1 IBI EN (19) Vref_B 2 Vref B Vref_A 5 Vref B [2] [5] Vref_B Vref A 2 | A1 33: [6] B1 <u>(18</u> В1 A1 3 A1 3 4 B1 Vref A Vref_B A2 33 131 B2 A2 4 (17) B2 GND 0 0 EN ₫<u>6</u> В3 A3 5 Thermal Pad A4 6 (<u>15</u>] B4 A5 [7] (14 B5 A6[≅ (13 B6 Α7 9) (<u>12</u> B7 A8 B8



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4 Revision History NOTE: Page numbers for previous revisions may differ to	rom page numbers in the current version.	
Changes from Revision J (April 2020) to Revision K	(May 2021) Pa	an

С	hanges from Revision J (April 2020) to Revision K (May 2021)	Page
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1
•	Updated the Bidirectional Translation section to include inclusive terminology	13
С	hanges from Revision I (June 2019) to Revision J (April 2020)	Page
•	Added section Voltage Translation for Vref_B < Vref_A + 0.8 V	16
C	hanges from Revision H (June 2019) to Revision I (July 2019)	Page
•	Changed product status from Advance Information mix to Production Data	1
•	Deleted Advance Information note from the DTQ package in the Device Information table	1
•	Deleted Advance Information note from DTQ package in the Pin Configuration and Functions section	ı <mark>4</mark>
•	Deleted Advance Information note for the DTQ package in the Thermal Information table	6
C	hanges from Revision G (February 2016) to Revision H (June 2019)	Page
•	Added Advance Information note to Device Information table for DTQ package	1
•	Added DTQ6 pinout drawing to Pin Configurations and Functions section (Advance Information)	4
•	Added Advance Information note to LSF0101 Thermal Information table.	<mark>6</mark>
•	General improvements to Application and Implementation section for clarity.	
C	hanges from Revision F (October 2015) to Revision G (October 2015)	Page
•	Added all available package dimensions in Device Information and changed the pin diagram descript	tion 1



Changes from Revision E (July 2015) to Revision F (October 2015)

Page

•	Changed Features from "Supports High Speed Translation, Greater Than 100 MHz" to "Supports Up to MHz Up Translation and Greater Than 100 MHz Down Translation at ≤ 30pF Cap Load and Up To 40 Nup/Down Translation at 50 pF Cap Load."	ИНz
•	Updated all propagation delay tables changed from generic to specific LSF devices.	
C	hanges from Revision D (October 2014) to Revision E (July 2015)	Page
•	Deleted "Less Than 1.5 ns Max Propagation Delay" from Features.	1

Updated ESD Ratings table.5

С	hanges from Revision C (May 2014) to Revision D (August 2014)	Page
•	Changed bidirectional voltage level translation from 1.0 to 0.95	1
•	Changed YZT package to fix view error	1
•	Changed YZT package to fix view error	4
	Added Vref. A footnote	13

Changes from Revision B (May 2014) to Revision C (May 2014)Page• Changed LSF0108 status from preview to production.1• Updated document title.1• Updated Handling Ratings table.5

Changes from Revision A (January 2014) to Revision B (February 2014)Page• Added LSF0108 to data sheet.1

С	hanges from Revision * (December 2013) to Revision A (January 2014)	Page
•	Updated part number	· · · · · · · · · · · · · · · · · · ·
•	Updated Electrical Characteristics table	



5 Pin Configuration and Functions

Pinout drawings are not to scale.

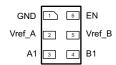


Figure 5-1. LSF0101 DRY Package 6-Pin SON Transparent Top View

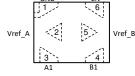


Figure 5-2. LSF0101 DTQ Package 6-Pin X2SON Transparent Top View

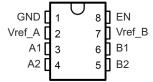


Figure 5-3. LSF0102 DCT or DCU Package 8-Pin SM8 or VSSOP Top View

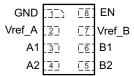


Figure 5-4. LSF0102 DQE Package 8-Pin X2SON Transparent Top View

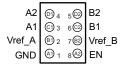


Figure 5-5. LSF0102 YZT Package 8-Pin DSBGA Bottom View

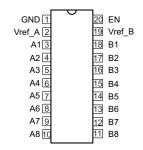


Figure 5-6. LSF0108 PW Package 20-Pin TSSOP Top View

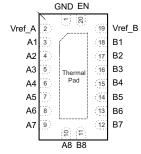


Figure 5-7. LSF0108 RKS Package 20-Pin VQFN Transparent Top View

Pin Functions

	PIN							
NAME	DCT, DCU, DQE, YZT NO.	DRY, DTQ NO.	PW or RKS NO.	I/O	DESCRIPTION			
An	3, 4	3	3 to 10	I/O	Auto Bidiractional Data port			
Bn	6, 5	4	18 to 11	I/O	Auto-Bidirectional Data port			
EN	8	6	20	I	Enable input; connect to Vref_B and pull-up through a high resis (200 kΩ). See Using the Enable Pin with the LSF Family			
GND	1	1	1	_	Ground			
Vref_A	2	2	2	_	Reference supply voltage.			
Vref_B	7	5	19	_	For proper device biasing, see Section 9 and Understanding the Bias Circuit for the LSF Family.			



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature (unless otherwise noted)(1)

				MIN	MAX	UNIT
VI	Input voltage ⁽²⁾			-0.5	7	V
V _{I/O}	Input/output voltage ⁽²⁾				7	V
	Continuous channel current				128	mA
I _{IK}	Input clamp current	\	< 0		-50	mA
T_{J}	Junction Temperature	·			150	°C
T _{stg}	Storage temperature range			-65	150	°C

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and input/output negative-voltage ratings may be exceeded if the input and input/output clamp-current ratings are observed.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatio discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
V _(ESD) Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{I/O}	Input/output voltage	0	5	V
V _{ref_A/B/EN}	Reference voltage	0	5	V
I _{PASS}	Pass transistor current		64	mA
T _A	Operating free-air temperature	-40	125	°C



6.4 Thermal Information: LSF0101, LSF0108

THERMAL METRIC ⁽¹⁾		LSF0	101	LSF		
		DTQ (X2SON)	DRY (SON)	RKS (VQFN)	PW (TSSOP)	UNIT
		6 PINS	6 PINS	20 PINS	20 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	294.4	407.0	49.3	106.6	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	188.9	285.2	45.9	41.0	°C/W
R _{θJB}	Junction-to-board thermal resistance	216.8	271.6	20.6	57.6	°C/W
ΨЈТ	Junction-to-top characterization parameter	26.5	113.5	2.5	4.2	°C/W
ΨЈВ	Junction-to-board characterization parameter	216.0	271.0	20.6	47.0	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	n/a	3.4	n/a	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

6.5 Thermal Information: LSF0102

		LSF0102				
THERMAL METRIC(1)		DCU (US8)	DCT (SM8)	DQE (X2SON)	YZT (DSBGA)	UNIT
		8 PINS	8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	210.1	189.6	246.5	125.5	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	89.1	119.6	149.1	1.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	88.8	102.1	100.0	62.7	°C/W
ΨЈТ	Junction-to-top characterization parameter	8.3	44.5	17.1	3.4	°C/W
ΨЈВ	Junction-to-board characterization parameter	88.4	101.0	99.8	62.7	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	n/a	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

6.6 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TE	EST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IK}	I _I = -18 mA,	V _{EN} = 0				-1.2	V
I _{IH}	V _I = 5 V	V _{EN} = 0				5.0	μA
Icc	$V_{ref_B} = V_{EN} = 5$.5 V, V _{ref_A} = 4.5	V or 1 V, I _O = 0, V _I = V _{CC} or GND		1		μΑ
C _{I(ref_A/B/EN)}	V _I = 3 V or 0				11		pF
C _{io(off)}	V _O = 3 V or 0,	V _{EN} = 0			4.0	6.0	pF
C _{io(on)}	V _O = 3 V or 0,	V _{EN} = 3 V			10.5	12.5	pF
			$V_{ref_A} = 3.3 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$		8.0		
	$V_I = 0$,	$I_O = 64 \text{ mA}$	$V_{ref_A} = 1.8 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$		9.0		Ω
			$V_{ref_A} = 1.0 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$		10		
	V _I = 0,	I _O = 32 mA	$V_{ref_A} = 1.8 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$		10		Ω
r _{on} ⁽²⁾	V ₁ - 0,	10 - 32 IIIA	$V_{ref_A} = 2.5 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$		15		22
	V _I = 1.8 V,	I _O = 15 mA	$V_{ref_A} = 3.3 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$		9.0		Ω
	V _I = 1.0 V,	I _O = 10 mA	$V_{ref_A} = 1.8 \text{ V}; V_{ref_B} = V_{EN} = 3.3 \text{ V}$		18		Ω
	V _I = 0 V,	I _O = 10 mA	$V_{ref_A} = 1.0 \text{ V}; V_{ref_B} = V_{EN} = 3.3 \text{ V}$		20		Ω
	V _I = 0 V,	I _O = 10 mA	V _{ref_A} = 1.0 V; V _{ref_B} = V _{EN} = 1.8 V		30		Ω

⁽¹⁾ All typical values are at $T_A = 25$ °C.

⁽²⁾ Measured by the voltage drop between the A and B pins at the indicated current through the switch. On-state resistance is determined by the lowest voltage of the two (A or B) pins.



6.7 LSF0101/02 AC Performance (Translating Down) Switching Characteristics , V_{GATE} = 3.3 V

over recommended operating free-air temperature range, $V_{GATE} = 3.3 \text{ V}$, $V_{IH} = 3.3 \text{ V}$, $V_{IL} = 0$, and $V_{M} = 1.15 \text{ V}$ (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50	pF	C _L = 30	pF	C _L = 15	pF	UNIT
PARAMETER	FROW (INPUT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	UNII
t _{PLH}	A or B	B or A	1.1		0.7		0.3		ns
t _{PHL}	AOIB	BOIA	1.2		0.8		0.4		115

6.8 LSF0108 AC Performance (Translating Down) Switching Characteristics, $V_{GATE} = 3.3 \text{ V}$

over recommended operating free-air temperature range, $V_{GATE} = 3.3 \text{ V}$, $V_{IH} = 3.3 \text{ V}$, $V_{IL} = 0$, and $V_{M} = 1.15 \text{ V}$ (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50	pF	C _L = 30	pF	C _L = 15	pF	UNIT
PARAMETER	FROW (INPUT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	UNII
t _{PLH}	A or B	B or A	1.9		1.4		0.75		no
t _{PHL}	AOIB	BOIA	2		1.5		0.85		ns

6.9 LSF0101/02 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, $V_{GATE} = 2.5 \text{ V}$, $V_{IH} = 2.5 \text{ V}$, $V_{IL} = 0$, and $V_{M} = 0.75 \text{ V}$ (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50	pF	C _L = 30	pF	C _L = 15	pF	UNIT
FARAMETER	FROW (INFOT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	ONII
t _{PLH}	A or B	B or A	1.2		0.8		0.35		ne
t _{PHL}	AUID	BULA	1.3		1		0.5		ns

6.10 LSF0108 AC Performance (Translating Down) Switching Characteristics, $V_{GATE} = 2.5 \text{ V}$

over recommended operating free-air temperature range, $V_{GATE} = 2.5 \text{ V}$, $V_{IH} = 2.5 \text{ V}$, $V_{IL} = 0$, and $V_{M} = 0.75 \text{ V}$ (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	(INPUT) TO (OUTPUT)		pF	C _L = 30	pF	C _L = 15	pF	UNIT
PARAMETER	PROW (INPUT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	UNII
t _{PLH}	A or B	B or A	2		1.45		0.8		ns
t _{PHL}	AOIB	BOIA	2.1		1.55		0.9		115

6.11 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 3.3 V

over recommended operating free-air temperature range, V_{GATE} = 3.3 V, V_{IH} = 2.3 V, V_{IL} = 0, V_{T} = 3.3 V, V_{M} = 1.15 V and R_{L} = 300 (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50	pF	C _L = 30	pF	C _L = 15	pF	UNIT
PARAMETER	PROW (INPUT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	UNII
t _{PLH}	A or B	B or A	1		0.8		0.4		ne
t _{PHL}	AOIB	BOIA	1		0.9		0.4		ns

6.12 LSF0108 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 3.3 V

over recommended operating free-air temperature range, $V_{GATE} = 3.3 \text{ V}$, $V_{IH} = 2.3 \text{ V}$, $V_{IL} = 0$, $V_{T} = 3.3 \text{ V}$, $V_{M} = 1.15 \text{ V}$ and $R_{L} = 300$ (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50	pF	C _L = 30	pF	C _L = 15	pF	UNIT
PARAMETER	PROW (INPOT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	ONII
t _{PLH}	A or B	B or A	2.1		1.55		0.9		ne
t _{PHL}	AOID	BOIA	2.2		1.65		1		ns



6.13 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, $V_{GATE} = 2.5 \text{ V}$

over recommended operating free-air temperature range, V_{GATE} = 2.5 V, V_{IH} = 1.5 V, V_{IL} = 0, V_{T} = 2.5 V, V_{M} = 0.75 V and R_{L} = 300 (unless otherwise noted) (see Figure 7-1)

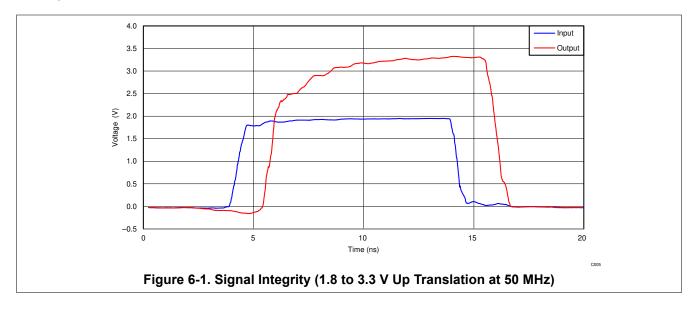
PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50	pF	C _L = 30	pF	C _L = 15	pF	UNIT
PARAMETER	PROW (INPUT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	UNII
t _{PLH}	A or B	B or A	1.1		0.9		0.45		ns
t _{PHL}	7 7016	BUIA	1.3		1.1		0.6		115

6.14 LSF0108 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, V_{GATE} = 2.5 V, V_{IH} = 1.5 V, V_{IL} = 0, V_{T} = 2.5 V, V_{M} = 0.75 V and R_{L} = 300 (unless otherwise noted) (see Figure 7-1)

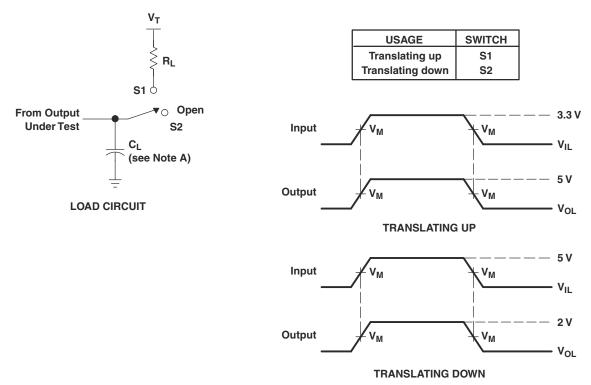
PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50	pF	C _L = 30	pF	C _L = 15	pF	UNIT	
PARAMETER	FROW (INPUT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	UNII	
t _{PLH}	A or B	B or A	1.8		1.35		0.8		ne	
t _{PHL}	AOIB	BOIA	1.9		1.45		0.9		ns	

6.15 Typical Characteristics





7 Parameter Measurement Information



NOTES: A. C_L includes probe and jig capacitance.

B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_{O} = 50 \Omega$, $t_{f} \leq$ 2 ns, $t_{f} \leq$ 2 ns.

C. The outputs are measured one at a time, with one transition per measurement.

Figure 7-1. Load Circuit for Outputs

8 Detailed Description

8.1 Overview

The LSF family can be used in level-translation applications for interfacing devices or systems operating with one another, that operate at different interface voltages. The LSF family is ideal for use in applications where an open-drain driver is connected to the data I/Os. With appropriate pull-up resistors and layout, LSF can achieve 100 MHz. The LSF family can also be used in applications where a push-pull driver is connected to the data I/Os. For an overview of device setup and operation, see *The Logic Minute* training series on *Understanding the LSF Family of Bidirectional, Multi-Voltage Level Translators*.

8.2 Functional Block Diagrams

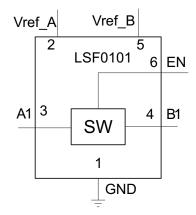


Figure 8-1. LSF0101 Functional Block Diagram

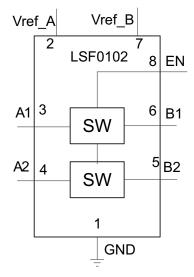


Figure 8-2. LSF0102 Functional Block Diagram

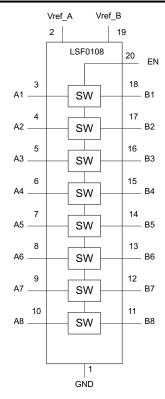


Figure 8-3. LSF0108 Functional Block Diagram

8.3 Feature Description

8.3.1 Auto Bidirectional Voltage Translation

All devices in the LSF family are auto bidirectional voltage level translators that are operational from 0.95 to 4.5 V on the Vref_A supply and from 1.8 to 5.5 V on the Vref_B supply. This allows bidirectional voltage translation between 0.95 V and 5.5 V without the need for a direction pin in open-drain or push-pull applications. LSF family supports level translation applications with transmission speeds greater than 100 Mbps for open-drain systems using a 30-pF capacitance and 250- Ω pullup resistor. For additional details on the recommended setup and operation of the LSF family of devices, see the *Understanding the LSF Family of Bidirectional, Multi-Voltage Level Translators* training series.

8.3.2 Output Enable

To enable the I/O pins, the EN input should be tied directly to Vref_B during operation. To ensure the high impedance state during power-up, power-down, or during operation, the EN pin must be LOW. The EN pin should always be tied directly to the Vref_B pin and is recommended to be disabled by an open-drain driver without a pullup resistor. For additional details on how to use the enable pin, see the *Using the Enable Pin with the LSF Family* video.

Table 8-1. Enable Pin Function Table

INPUT EN ⁽¹⁾ PIN	Data Port State
Tied directly to Vref_B	An = Bn
L	Hi-Z

(1) EN is controlled by V_{ref B} logic levels.

8.4 Device Functional Modes

For each channel (n), when either the An or Bn port is LOW, the switch provides a low impedance path between the An and Bn ports; the corresponding Bn or An port will be pulled LOW. The low R_{ON} of the switch allows connections to be made with minimal propagation delay and signal distortion.

When the signal is being driven from Bn to An and the Bn port is driven HIGH, the switch will be OFF, clamping the voltage on the An port to the voltage set by Vref_A. When the signal is being driven from A to B and the An port is HIGH, the switch will be OFF and the Bn port will then driven to a voltage higher than Vref_A by the pullup resistor that is connected to the pull-up supply voltage (V_{pu#}). This functionality allows seamless translation between higher and lower voltages selected by the user, without the need for directional control.

Refer to Table 8-1 for a summary of device operation. For additional details on the functional operation of the LSF family of devices, see the *Down Translation with the LSF Family* and *Up Translation with the LSF Family* videos.

Table 8-2. Device Functionality

Signal Direction ⁽¹⁾	Input State	Switch State	Functionality
B to A (Down Translation)	B = LOW	ON (Low Impedance)	A-side voltage is pulled low through the switch to the B-side voltage
B to A (Down Translation)	B = HIGH	OFF (High Impedance)	A-side voltage is clamped at Vref_A ⁽²⁾
A to B (Up Translation)	A = LOW	ON (Low Impedance)	B-side voltage is pulled low through the switch to the A-side voltage
A to B (op Translation)	A = HIGH	OFF (High Impedance)	B-side voltage is clamped at Vref_A and then pulled up to the Vpu# supply voltage

- (1) The downstream channel should not be actively driven through a low impedance driver, or else there may be bus contention.
- (2) The A-side can have a pullup to Vref_A for additional current drive capability or may also be pulled above Vref_A with a pullup resistor. Specifications in the Section 6.3 should always be followed.

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The LSF devices are able to perform voltage translation for open-drain or push-pull interfaces. Table 9-1 provides common interfaces and the corresponding device recommendation from the LSF family which supports the corresponding bit count.

Table 9-1. Voltage Translator for Common Interfaces

Part Name	Channel Number	Interface
LSF0101	1	GPIO
LSF0102	2	GPIO, MDIO, SMBus, PMBus, I ² C
LSF0108	8	GPIO, MDIO, SDIO, SVID, UART, SMBus, PMBus, I ² C, SPI

9.2 Typical Applications

9.2.1 Open-Drain Interface (I²C, PMBus, SMBus, GPIO)

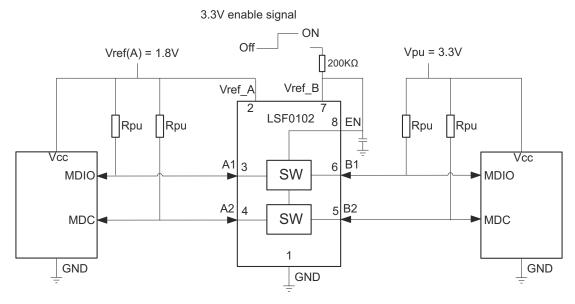


Figure 9-1. Typical Application Circuit for Open-Drain Translation (MDIO shown as an example)

9.2.1.1 Design Requirements

9.2.1.1.1 Enable, Disable, and Reference Voltage Guidelines

The LSF family has an EN input that is used to disable the device by setting EN LOW, placing all I/Os in the high-impedance state. Since the LSF family of devices are switch-type voltage translators, the power consumption is very low. TI recommends always enabling the LSF family for bidirectional applications (I²C, SMBus, PMBus, or MDIO).

The state of the s									
	PARAMETER	MIN	TYP	MAX	UNIT				
Vref_A ⁽¹⁾	reference voltage (A)	0.95		4.5	V				
Vref_B	reference voltage (B)	Vref_A + 0.8		5.5	V				
V _{I(EN)}	input voltage on EN pin	Vref_A + 0.8		5.5	V				
Vpu	pull-up supply voltage	0		Vref_B	V				

Table 9-2. Application Operating Condition

(1) Vref A is required to be the lowest voltage level across all inputs and outputs.

The 200 k Ω , pull-up resistor is required to allow Vref_B to regulate the EN input and properly bias the device for translation. For additional details on device biasing, see the *Understanding the Bias Circuit for the LSF Family* video. A filter capacitor on Vref_B is recommended. Also Vref_B and V_{I(EN)} are recommended to be 1.0 V higher than Vref_A for best signal integrity.

9.2.1.2 Detailed Design Procedure

9.2.1.2.1 Bidirectional Translation

For the bidirectional translation configuration (higher voltage to lower voltage or lower voltage to higher voltage), the EN input must be connected to Vref_B and both pins must be pulled up to the HIGH side Vpu through a pull-up resistor (typically 200 k Ω). This allows Vref_B to regulate the EN input and bias the channels for proper translation. A filter capacitor on Vref_B is recommended for a stable supply at the device. The controller output driver can be push-pull or open-drain (pull-up resistors may be required) and the peripheral device output can be push-pull or open-drain (pull-up resistors are required to pull the Bn outputs to Vpu).

If either output is push-pull, data must be unidirectional or the outputs must be tri-state and be controlled by some direction-control mechanism to prevent HIGH-to-LOW bus contention in either direction. If both outputs are open-drain, no direction control is needed.

When Vref_B is connected through a 200-kΩ resistor to a 3.3-V Vpu power supply and Vref_A is set 1.8 V, as shown in Figure 9-1, the A1 and A2 channels have a maximum output voltage equal to Vref_A, and the B1 and B2 channels have has a maximum output voltage equal to Vpu.

9.2.1.2.2 Pull-up Resistor Sizing

The pull-up resistor value needs to limit the current through the pass transistor when it is in the ON state to about 15 mA. This ensures a voltage drop of 260 mV to 350 mV to have a valid LOW signal on the downstream channel. If the current through the pass transistor is higher than 15 mA, the voltage drop is also higher in the ON state. To set the current through each pass transistor at 15 mA, calculate the pull-up resistor value using the following equation:

$$Rpu = (Vpu - 0.35 V) / 0.015 A$$
 (1)

Table 9-3 summarizes resistor values, reference voltages, and currents at 15 mA, 10 mA, and 3 mA. The resistor value shown in the +10% column (or a larger value) should be used to ensure that the voltage drop across the transistor is 350 mV or less. The external driver must be able to sink the total current from the resistors on both sides of the LSF family device at 0.175 V, although the 15 mA applies only to current flowing through the LSF family device.

Table 3-3. I un-up Resistor Values										
V (1) (2)	15	mA	10	mA	3 mA					
V _{DPU} (1) (2)	NOMINAL (Ω)	+10% ⁽³⁾ (Ω)	NOMINAL (Ω)	+10% ⁽³⁾ (Ω)	NOMINAL (Ω)	+10% ⁽³⁾ (Ω)				
5 V	310	341	465	512	1550	1705				
3.3 V	197	217	295	325	983	1082				
2.5 V	143	158	215	237	717	788				
1.8 V	97	106	145	160	483	532				
1.5 V	77	85	115	127	383	422				
1.2 V	57	63	85	94	283	312				

Table 9-3. Pull-up Resistor Values

9.2.1.3 Application Curve

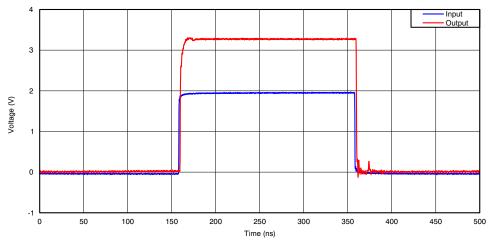


Figure 9-2. Open Drain Translation (1.8 V to 3.3 V at 2.5 MHz)

⁽¹⁾ Calculated for $V_{OL} = 0.35 \text{ V}$

⁽²⁾ Assumes output driver V_{OL} = 0.175 V at stated current

^{(3) +10%} to compensate for V_{DD} range and resistor tolerance



9.2.2 Mixed-Mode Voltage Translation

The supply voltage ($V_{pu\#}$) for each channel can be individually set with a pull-up resistor. An example of this mixed-mode multi-voltage translation is shown in Figure 9-3. For additional details on multi-voltage translation, see the *Multi-voltage Translation with the LSF Family* video.

With the Vref_B pulled up to 5V and Vref_A connected to 1.8V, all channels will be clamped to 1.8V at which point a pullup can be used to define the high level voltage for a given channel.

- Push-Pull Down Translation (5V to 1.8V): Channel 1 is an example of this setup. When B1 is 5V, A1 is clamped to 1.8V, and when B1 is LOW, A1 is driven LOW through the switch.
- Push-Pull Up Translation (1.8V to 5V): Channel 2 is an example of this setup. When A2 is 1.8V, the switch is high impedance and the B2 channel is pulled up to 5V. When A2 is LOW, B2 is driven LOW through the switch.
- Push-Pull Down Translation (3.3V to 1.8V): Channels 3 and 4 are examples of this setup. When either B3 or B4 are driven to 3.3V, A3 or A4 are clamped to 1.8V, and when either B3 or B4 are LOW, A3 or A4 are driven LOW through the switch.
- Open-Drain Bidirectional Translation (3.3V ↔ 1.8V): Channels 5 through 8 are examples of this setup. These channels are for bidirectional operation for I²C and MDIO to translate between 1.8V and 3.3V with open-drain drivers.

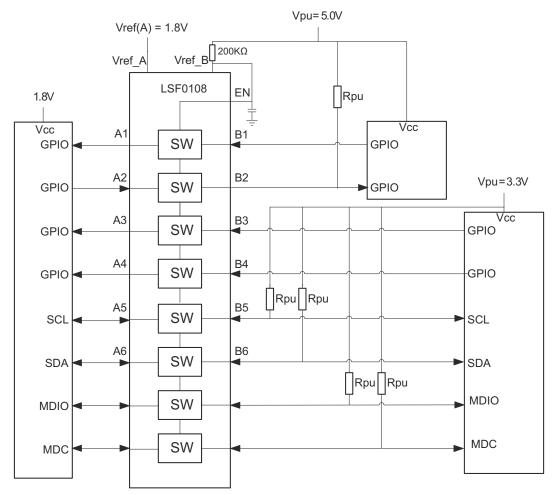


Figure 9-3. Multi-Voltage Translation with the LSF0108

9.2.3 Voltage Translation for Vref B < Vref A + 0.8 V

As described in Table 9-2, it is generally recommended that Vref_B > Vref_A + 0.8 V; however, the device can still be operated in the condition where Vref_B < Vref_A + 0.8 V as long as additional considerations are made for the design.

Typical Operation (Vref_B > Vref_A + 0.8 V): In this scenario, pullup resistors are not required on the A-side for proper down-translation as is shown for channels 1 and 2 of Figure 9-3. The typical operating mode of the device ensures that when down translating from B to A, the A-side I/O ports will clamp at Vref_A to provide proper voltage translation. For further explanation of device operation, see the *Down Translation with the LSF Family* video.

Requirements for Vref_B < Vref_A + 0.8 V Operation: In this scenario, there is not a large enough voltage difference between Vref_A and Vref_B to ensure that the A side I/O ports will be clamped at Vref_A, but rather at a voltage approximately equal to Vref_B - 0.8V. For example, if Vref_B = 1.8V and Vref_A = 1.2V, the A-side I/Os will clamp to a voltage around 1.0V. Therefore, to operate in such a condition, the following additional design considerations must be met:

- Vref_B must be greater than Vref_A during operation (Vref_B > Vref_A)
- Pullup resistors should be populated on A-side I/O ports to ensure the line will be fully pulled up to the desired voltage

An example of this setup is shown in Figure 9-4, where $1.2V \leftrightarrow 1.8V$ translation is achieved with the LSF0102. This type of setup also applies for other voltage nodes such as $1.8V \leftrightarrow 2.5V$, $1.05V \leftrightarrow 1.5V$, and others as long as the Section 6.3 table is followed.

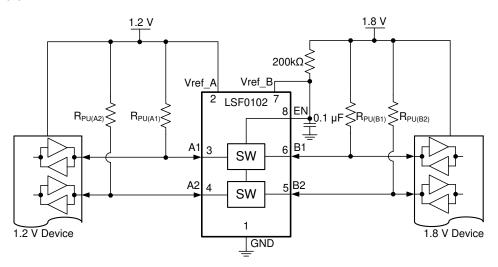


Figure 9-4. 1.2 to 1.8V Level Translation with LSF0102



10 Power Supply Recommendations

There are no power sequence requirements for the LSF family. For recommended operating voltages for all supply and input pins, see Table 10-1.

Table 10- 1	I. Recommended	Operating	Voltages
--------------------	----------------	-----------	----------

	PARAMETER	MIN	TYP MAX	UNIT
Vref_A ⁽¹⁾	reference voltage (A)	0.95	4.5	V
Vref_B	reference voltage (B)	Vref_A + 0.8	5.5	V
V _{I(EN)}	input voltage on EN pin	Vref_A + 0.8	5.5	V
Vpu	pull-up supply voltage	0	Vref_B	V

11 Layout

11.1 Layout Guidelines

Because the LSF family is a switch-type level translator, the signal integrity is highly related with a pull-up resistor and PCB capacitance condition.

- · Short signal trace as possible to reduce capacitance and minimize stub from pull-up resistor.
- Place LSF close to high voltage side.
- Select the appropriate pull-up resistor that applies to translation levels and driving capability of transmitter.

11.2 Layout Example

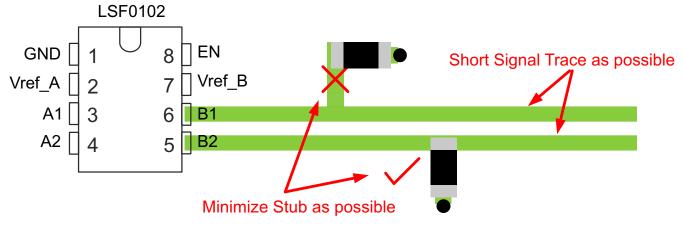


Figure 11-1. Short Trace Layout

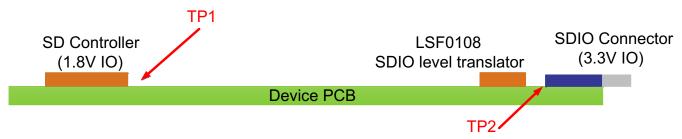


Figure 11-2. Device Placement

12 Device and Documentation Support

12.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 12-1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
LSF0101	Click here	Click here	Click here	Click here	Click here
LSF0102	Click here	Click here	Click here	Click here	Click here
LSF0108	Click here	Click here	Click here	Click here	Click here

- 1. LSF Translator Family Evaluation Module
- 2. The Logic Minute Video Training Series on Understanding the LSF Family of Devices
 - Introduction Voltage Level Translation with the LSF Family
 - Understanding the Bias Circuit for the LSF Family
 - Using the Enable Pin with the LSF Family
 - Translation Basics with the LSF Family
 - Down Translation with the LSF Family
 - Up Translation with the LSF Family
 - Multi-Voltage Translation with the LSF Family
 - Single Supply Translation with the LSF Family
- 3. Voltage Level Translation with the LSF Family Application Note
- 4. Biasing Requirements for TXS, TXB, and LSF Auto-Bidirectional Translators Application Note

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.



13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
LSF0101DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD	Samples
LSF0101DTQR	ACTIVE	X2SON	DTQ	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	FC	Samples
LSF0102DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	NG2 (S, Y)	Samples
LSF0102DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(G2, NG2J, NG2P, N G2S) NY	Samples
LSF0102DQER	ACTIVE	X2SON	DQE	8	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	RV	Samples
LSF0102YZTR	ACTIVE	DSBGA	YZT	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	RV	Samples
LSF0108PWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LSF0108	Samples
LSF0108RKSR	ACTIVE	VQFN	RKS	20	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LSF0108	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

PACKAGE OPTION ADDENDUM

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(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF LSF0102, LSF0108:

Automotive: LSF0102-Q1, LSF0108-Q1

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

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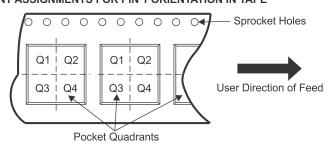
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LSF0101DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
LSF0101DTQR	X2SON	DTQ	6	3000	180.0	9.5	0.94	1.13	0.5	2.0	8.0	Q2
LSF0102DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.25	3.4	1.0	4.0	8.0	Q3
LSF0102DQER	X2SON	DQE	8	5000	180.0	9.5	1.15	1.6	0.5	4.0	8.0	Q1
LSF0102YZTR	DSBGA	YZT	8	3000	180.0	8.4	1.02	2.02	0.75	4.0	8.0	Q1
LSF0108PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
LSF0108RKSR	VQFN	RKS	20	3000	177.8	12.4	2.73	4.85	1.03	4.0	12.0	Q1

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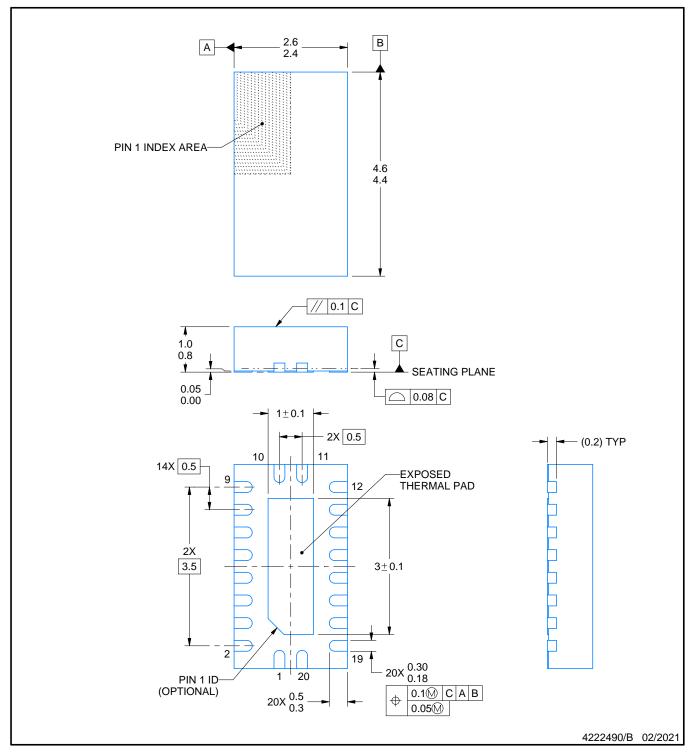


*All dimensions are nominal

di diriensions are nomina							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LSF0101DRYR	SON	DRY	6	5000	184.0	184.0	19.0
LSF0101DTQR	X2SON	DTQ	6	3000	189.0	185.0	36.0
LSF0102DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
LSF0102DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
LSF0102DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
LSF0102DQER	X2SON	DQE	8	5000	184.0	184.0	19.0
LSF0102YZTR	DSBGA	YZT	8	3000	182.0	182.0	20.0
LSF0108PWR	TSSOP	PW	20	2000	364.0	364.0	27.0
LSF0108RKSR	VQFN	RKS	20	3000	202.0	201.0	28.0



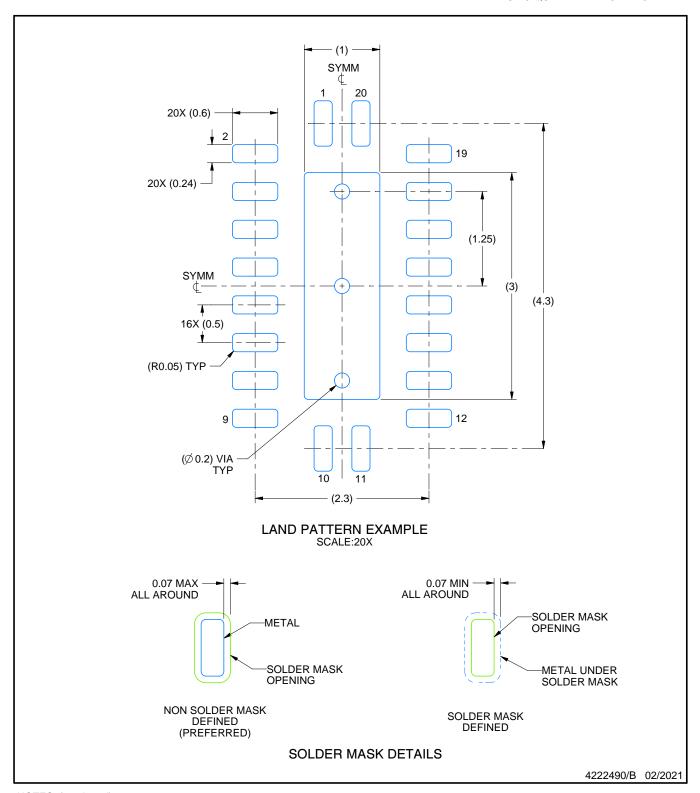
PLASTIC QUAD FLATPACK - NO LEAD



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

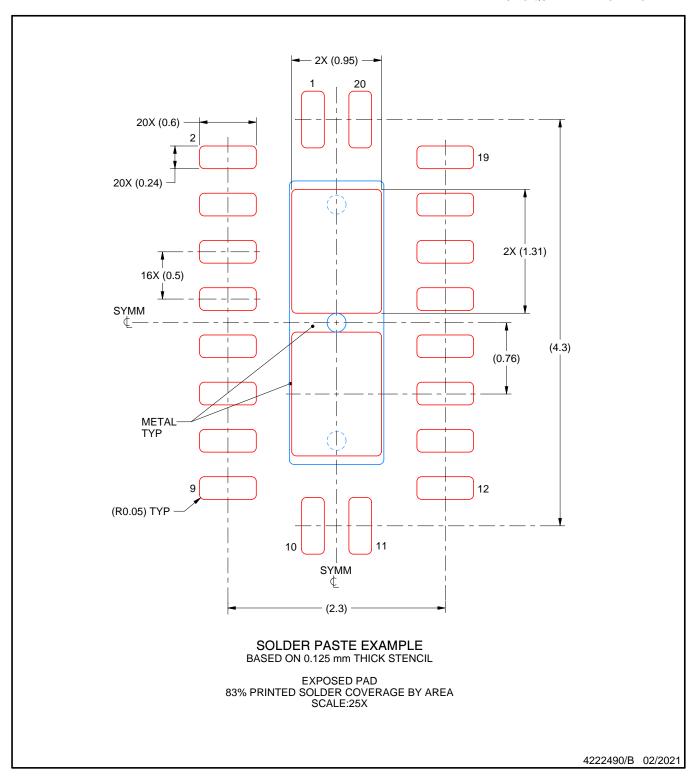


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



PLASTIC QUAD FLATPACK - NO LEAD

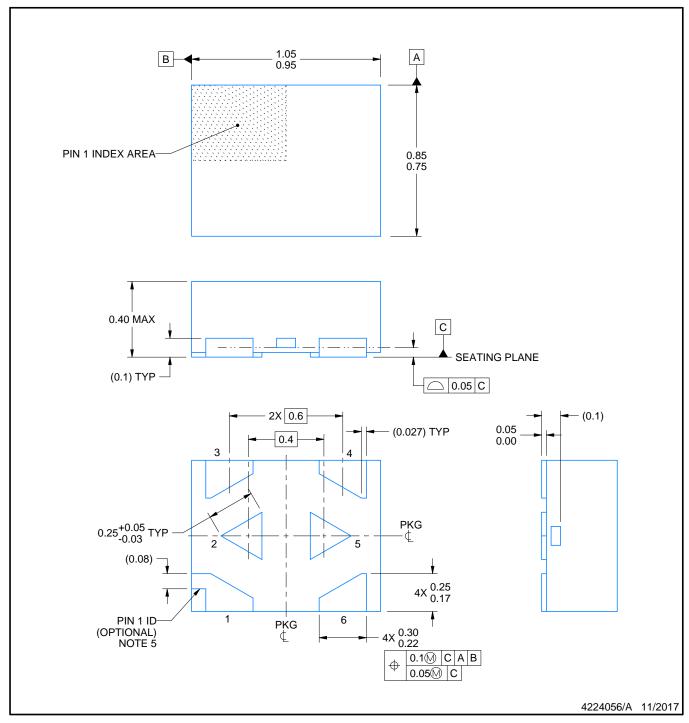


NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



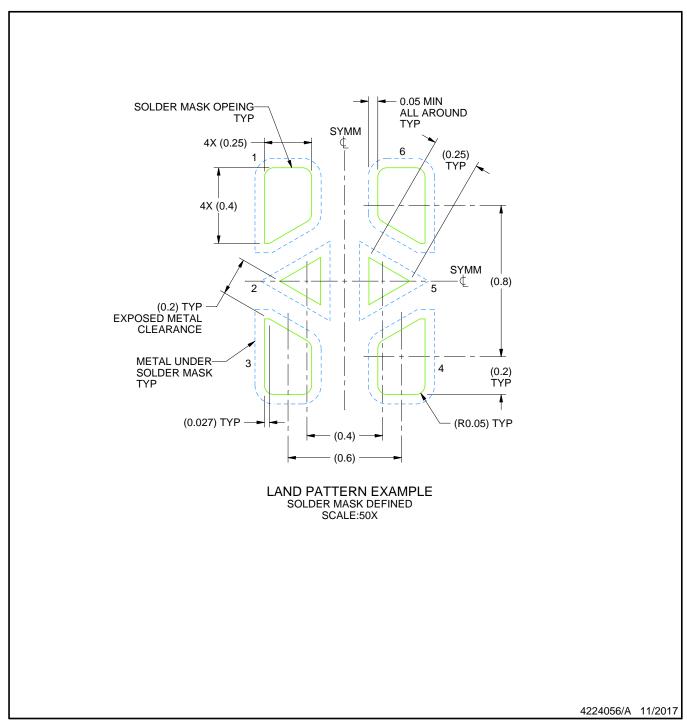




- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pads must be soldered to the printed circuit board for optimal thermal and mechanical performance.

 4. The size and shape of this feature may vary.
- 5. Features may not exist. Recommend use of pin 1 marking on top of package for orientation purposes.



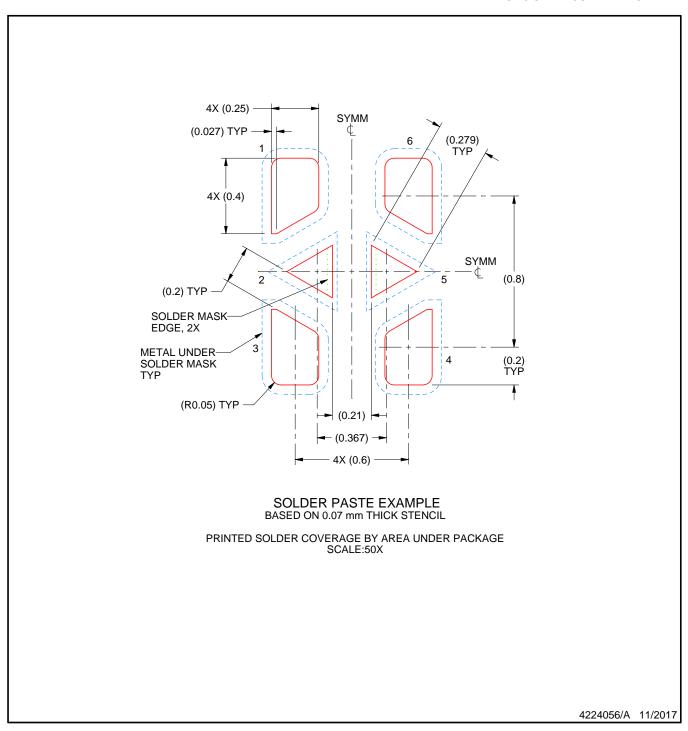


NOTES: (continued)



^{6.} This package is designed to be soldered to a thermal pads on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

^{7.} Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
 C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.







- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This package complies to JEDEC MO-287 variation X2EAF.





NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).





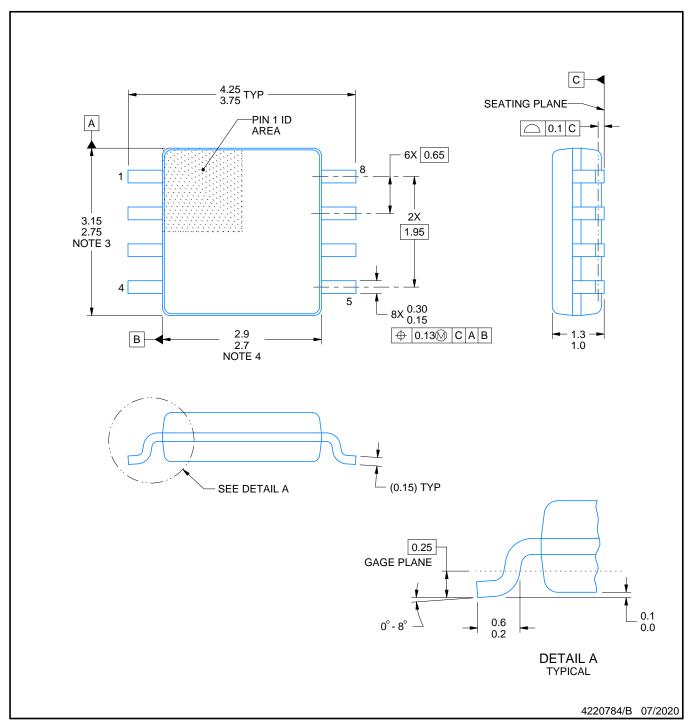
NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





SMALL OUTLINE PACKAGE



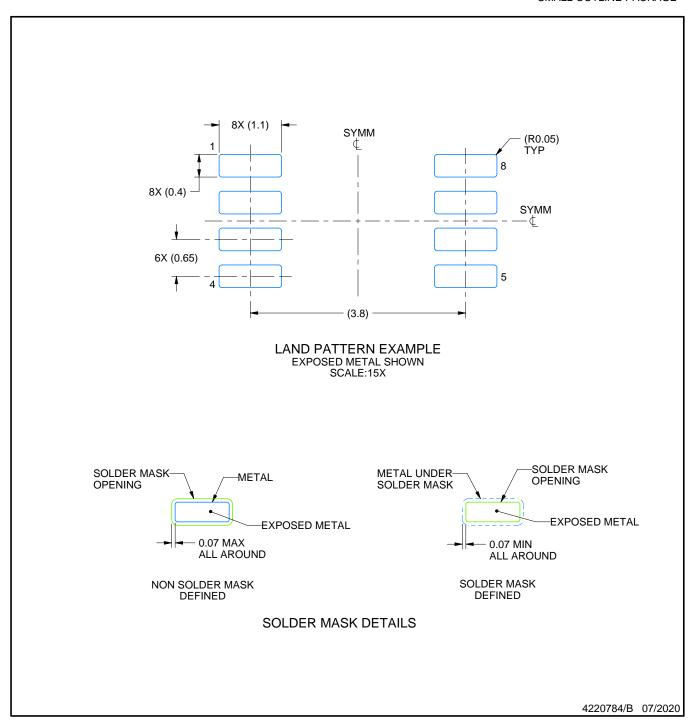
- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MS-187.



SMALL OUTLINE PACKAGE

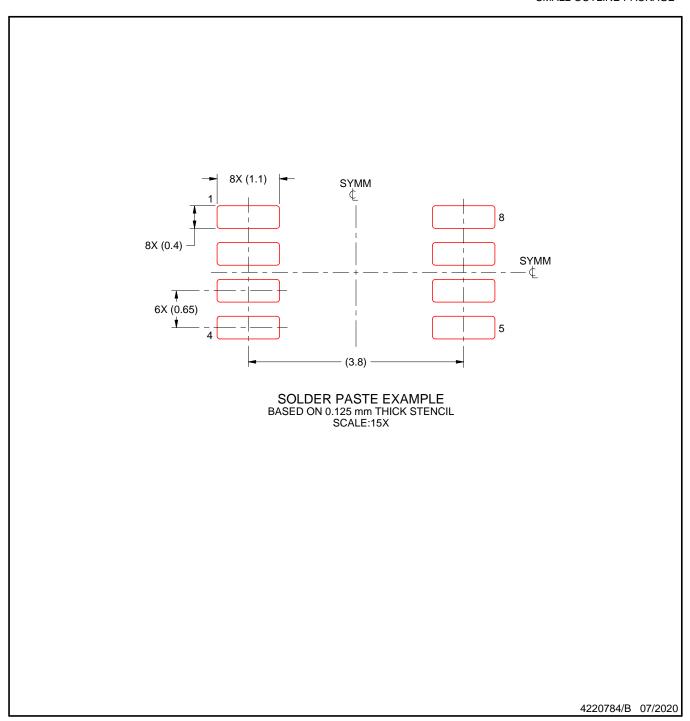


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



- : A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-187 variation CA.



DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.









- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.





NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).





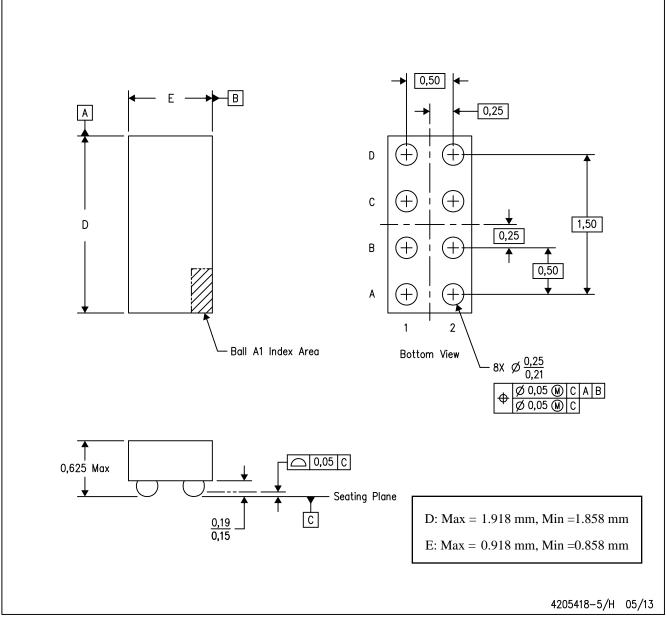
NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



YZT (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.



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